

# Investigation of LGAD performance dependence on neutron flux

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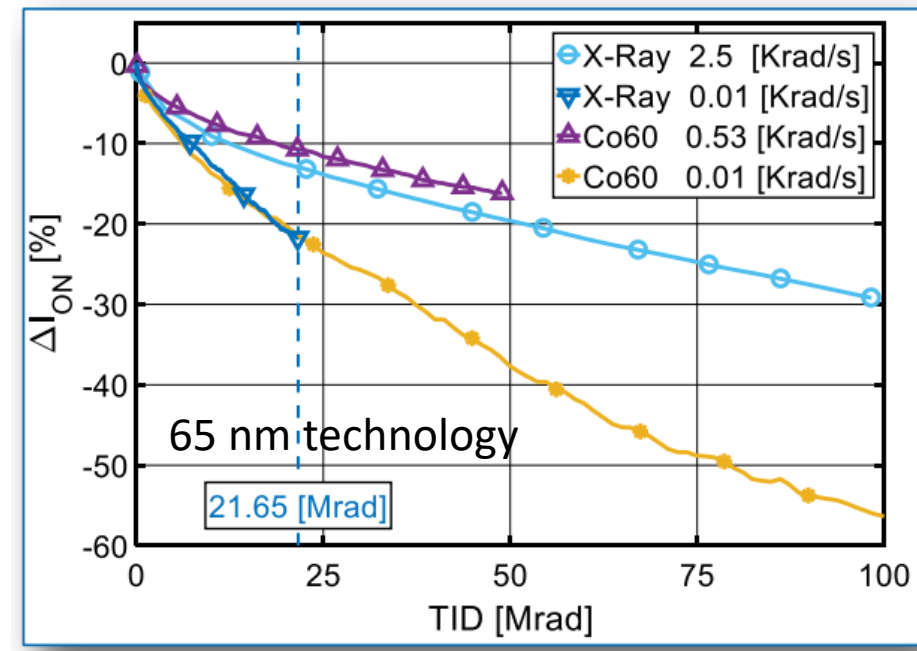
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A BROAD COLLABORATION WITH ATLAS-HGTD GROUPS

# Motivation

- LGADs will at HL-LHC be exposed to fluxes of particles around  $10^7$ - $10^8$   $\text{cm}^2 \text{s}^{-1}$
- Most of the irradiation studies done so far use fluxes which are much larger than that (typically  $\sim 10^{12}$   $\text{cm}^2 \text{s}^{-1}$  at JSI reactor )
- Dose rate effects observed in electronics and present a major problem (depends on bias/temperature/annealing) – safety factors
- Question do we see that also in the bulk?
  - studies showed no flux effect on  $N_{\text{eff}}$  and  $I_{\text{leak}}$  (D. Zontar PhD thesis)
  - effects to removal of initial dopants was not studied to our knowledge
- Possible dependence of initial acceptor removal rate would have a large implication to operation of LGADs at HL-LHC
  - positive in case of smaller removal at low rates
  - negative in case of larger removal at low rates



F. Faccio, HSTD11, Okinawa, 2017

# Reasons for possible flux effects

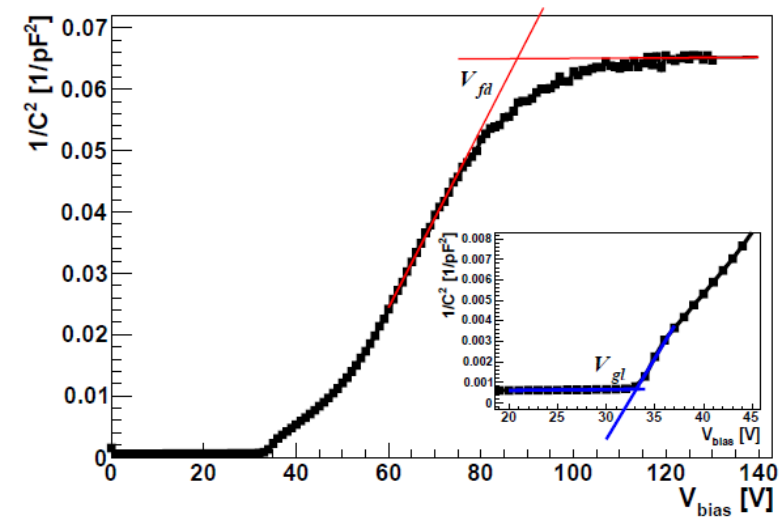
- The main channel for removal of initial acceptors is:  $B_s + Si_i \rightarrow B_i$  which is followed by reactions of  $B_i$  with other impurities and defects
- Different mobilities of Vacancies (V) and Interstitials (I) can lead to different recombination rate of V-I if more are created close in space and time and don't have time to react with other impurities/defects
- Smaller recombination could effectively lead to larger removal at low fluxes ☹️
- As the mechanisms are not fully known checks are required.

# Samples used in the study

- LGADs from ATLAS-HGTD prototype run with HPK were used – they're different in implant dose and also in depth profile of the implant

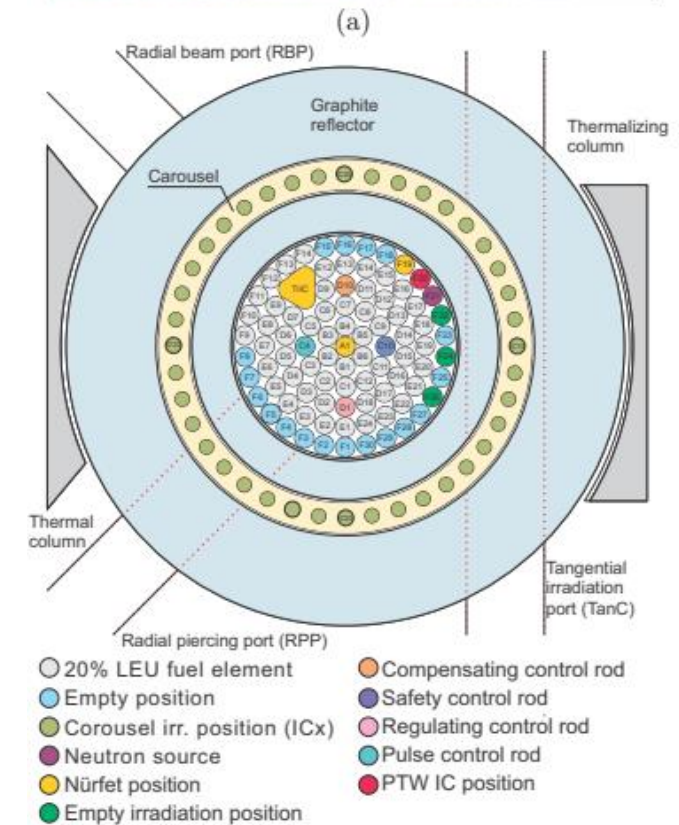
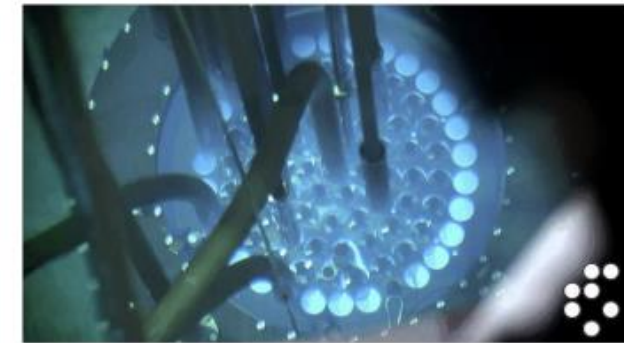
Sample name	Thickness	V <sub>gl</sub> [V]	V <sub>fd</sub> [V]
HPK-3.1-50	50 μm	42	49
HPK-3.2-50	50 μm	56	64

- Samples were studied with
  - CV/IV at 20°C and 10 kHz to determine V<sub>gl</sub>, V<sub>fd</sub>
  - Timing setup to verify that there is no impact to timing performance as well
- All samples were annealed for 80min @ 60°C after irradiation to wipe out different history during irradiations
- The temperature during irradiations is not controlled – at full power in F19 irradiations <50°C



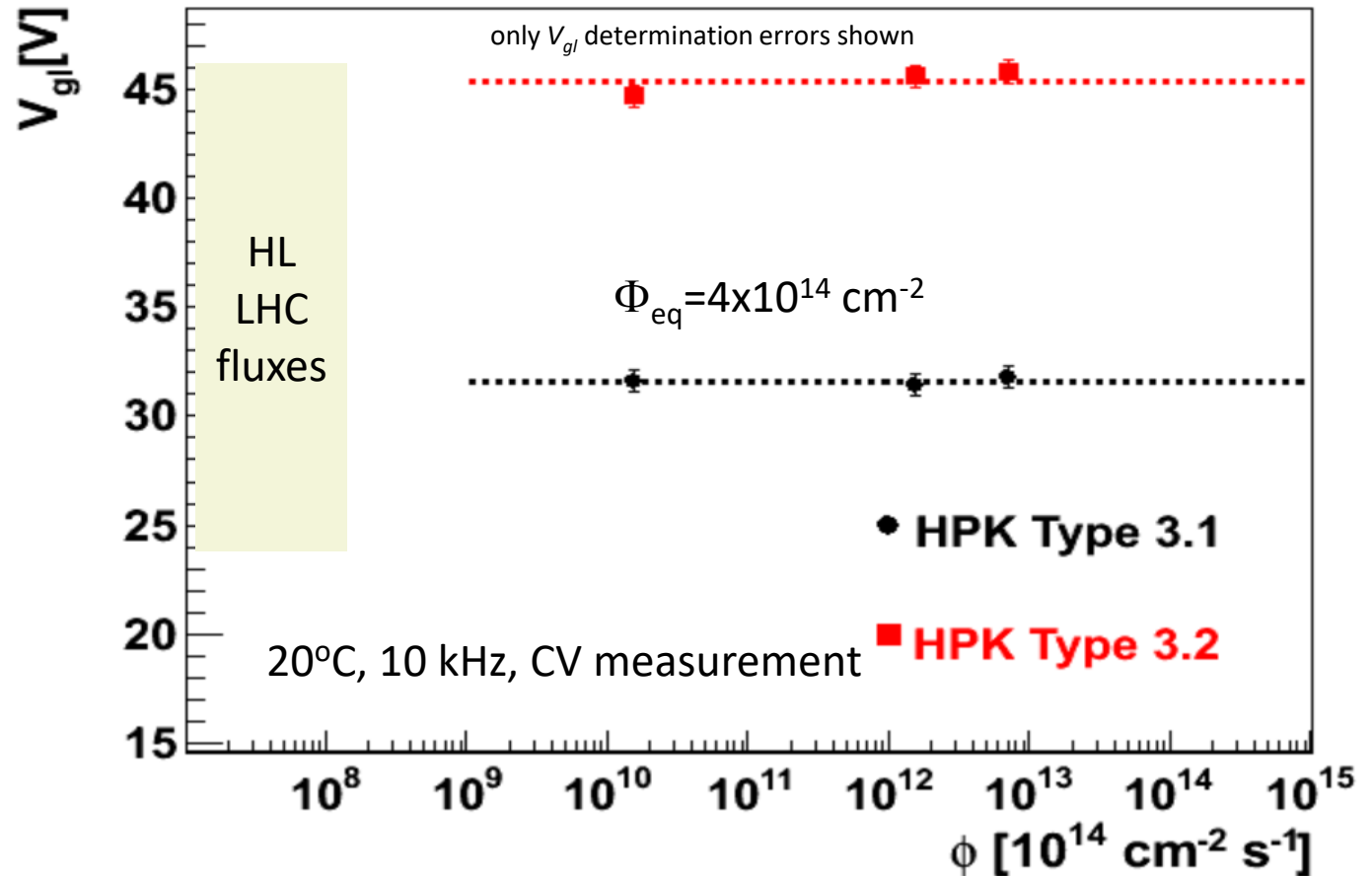
# Irradiations

- Samples were irradiated with reactor neutrons at three different fluxes
  - $1.55 \times 10^{12} \text{ cm}^{-2} \text{ s}^{-1}$  (250 kW, F19 channel – our standard irradiation flux)
  - $1.55 \times 10^{10} \text{ cm}^{-2} \text{ s}^{-1}$  (2.5 kW, F19 channel)
  - $7 \times 10^{12} \text{ cm}^{-2} \text{ s}^{-1}$  (250 kW, Central channel)
- All samples were irradiated to the **same fluence of  $4 \times 10^{14} \text{ cm}^{-2}$** 
  - Effects on  $V_{gl}$  are clearly visible
  - Timing measurement can be accurately performed
  - A wide flux range can be practically studied
    - 26000 s for slow (F19)
    - 260 s for standard (F19)
    - 57 s for fast (CK)



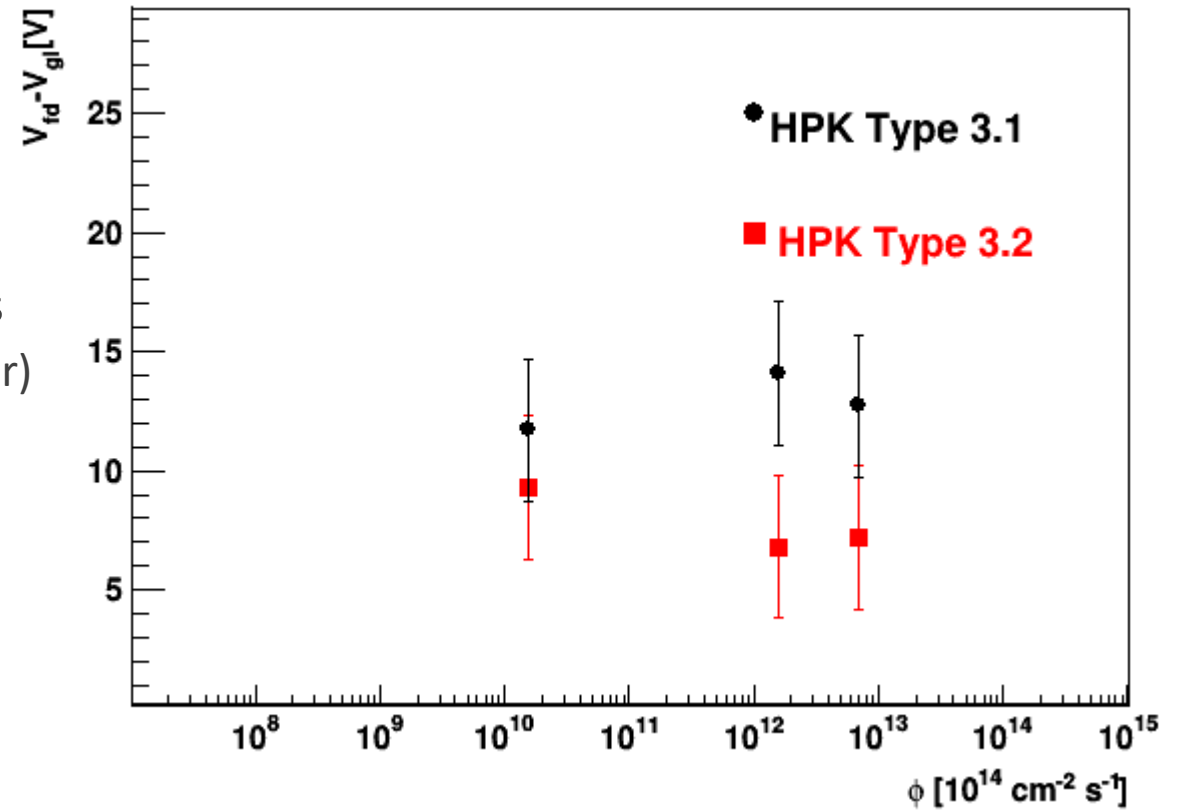
# Measurements of gain layer depletion $V_{gl}$

- There is no flux impact on  $V_{gl}$  for both investigated samples with different implant profiles
- We are still two orders of magnitude away from HL-LHC fluxes, but the flux rate seem not to play a role on effective acceptor removal
- Estimation of  $V_{gl}$  uncertainty:
  - uncertainty due to 10% in fluence  $\rightarrow \delta V_{gl} \sim 1V$
  - uncertainty due to  $V_{gl}$  determination  $\rightarrow \delta V_{gl} \sim 0.4 V$
  - uncertainty due to initial material  $\sim 1\% \rightarrow \delta V_{gl} \sim 0.5 V$
- Fits are compatible with hypothesis of acceptor removal not depending of flux.



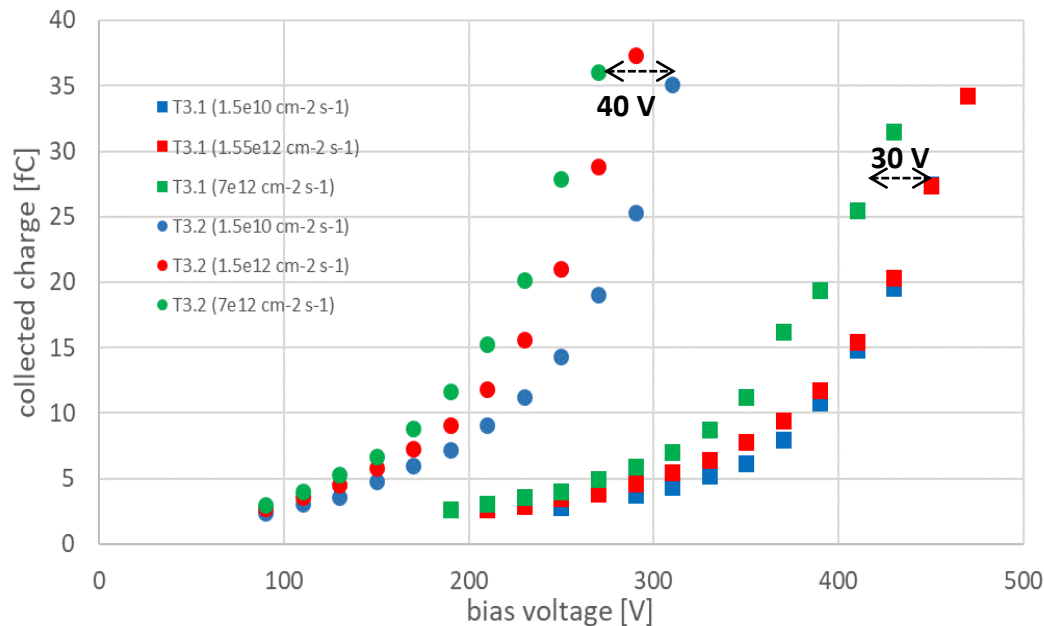
# Depletion of the bulk

- There is no flux impact on bulk depletion voltage for both investigated samples with different implant profiles
- The result is in agreement with previous observations
  - more difficult to determine the  $V_{fd}$  (larger systematic error)
  - if full initial acceptor removal is assumed deep acceptor introduction rate  $g_{eff}=0.01-0.016 \text{ cm}^{-1}$  is compatible with standard introduction rate in FZ



# Charge and Timing measurements

- At high voltages there may be effects not revealed by  $V_{fd}$  and  $V_{gl}$  measurements and may impact timing resolution and charge collection
- CC and timing measurements are the ultimate benchmark, therefore all detectors were tested with  $^{90}\text{Sr}$  setup to very high bias voltages for performance
- The performance differs slightly for different samples, but the difference is compatible with known uncertainties:
  - T3.2:  $\Delta V(35 \text{ fC}) \sim 40\text{V} \rightarrow \Delta V_{gl}(2 \mu\text{m}) \sim 1.4\text{-}1.6 \text{ V}$  are required to increase the field in gain layer by  $0.8 \text{ V}/\mu\text{m} \rightarrow$  measured difference is  $\Delta V_{gl} = 1.1 \text{ V}$
  - T3.1:  $\Delta V(30 \text{ fC}) \sim 30\text{V} \rightarrow \Delta V_{gl}(1 \mu\text{m}) \sim 0.6 \text{ V}$  are required to increase the field in gain layer by  $0.6 \text{ V}/\mu\text{m} \rightarrow$  measured difference is  $\Delta V_{gl} = 0.4 \text{ V}$
- **Small difference between the samples can be to large extent explained by the small difference in  $V_{gl}$**



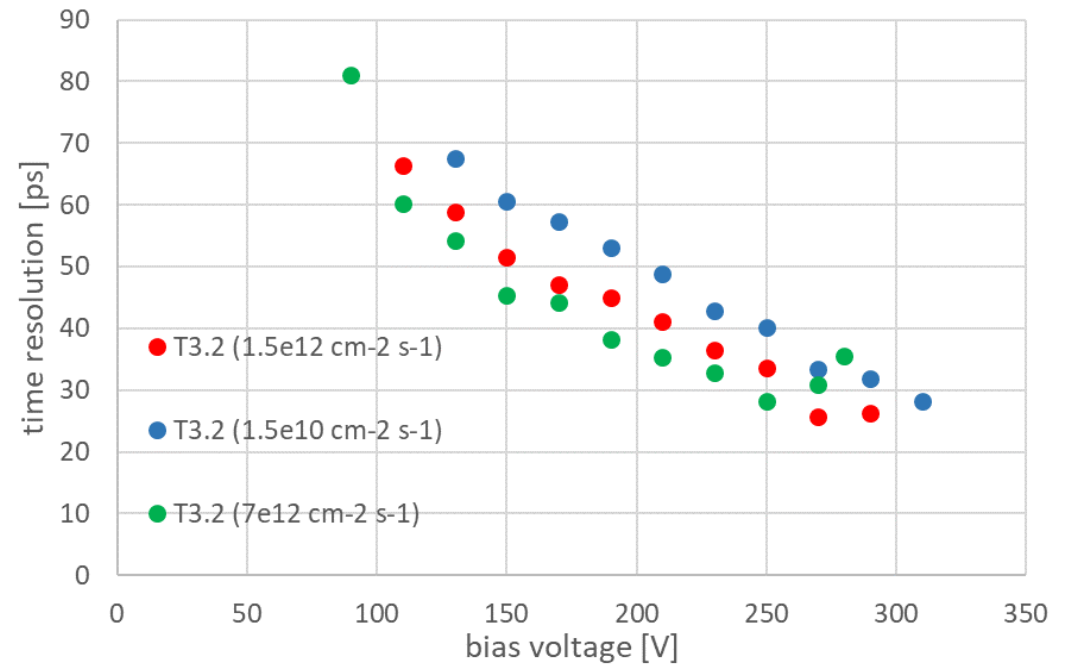
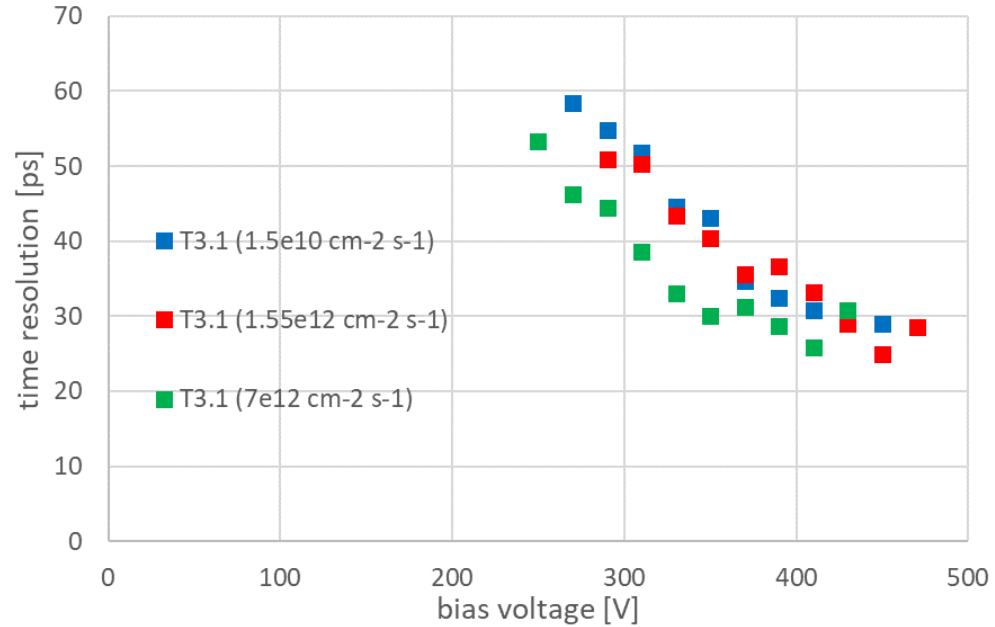
Note the error on fluence may be larger for central channel:

- 57s irradiation time – few s already mean sizeable effect
- less calibration runs were performed – not so well calibrated

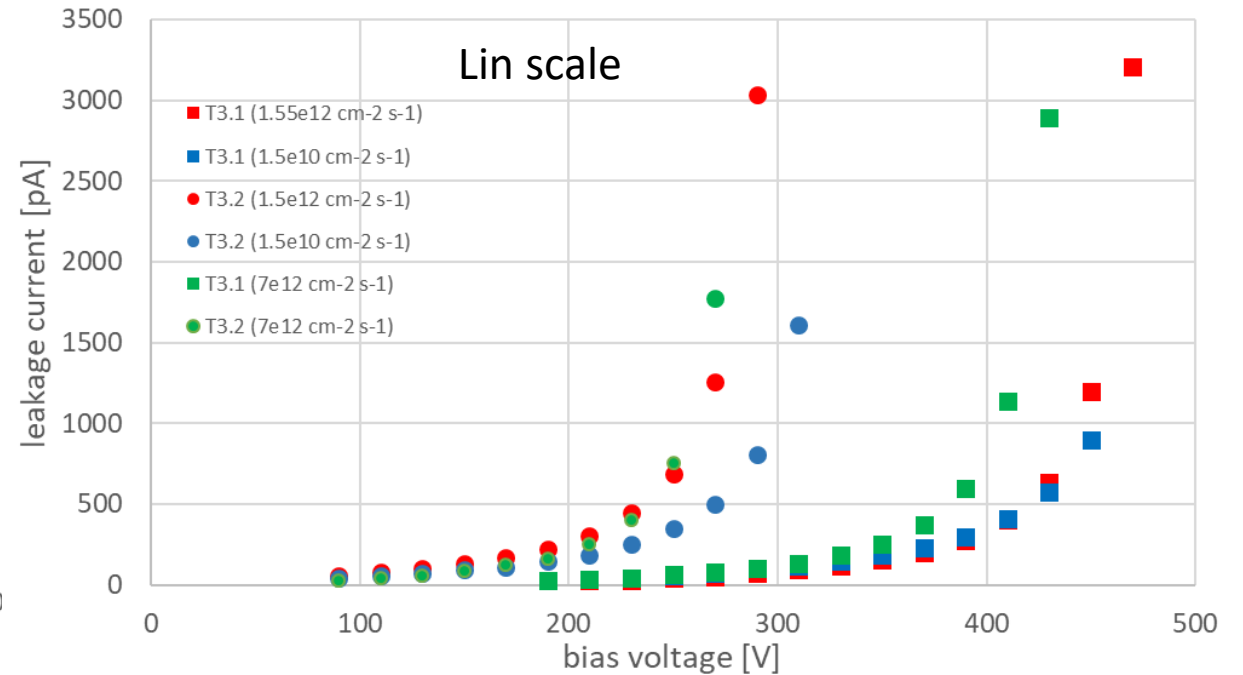
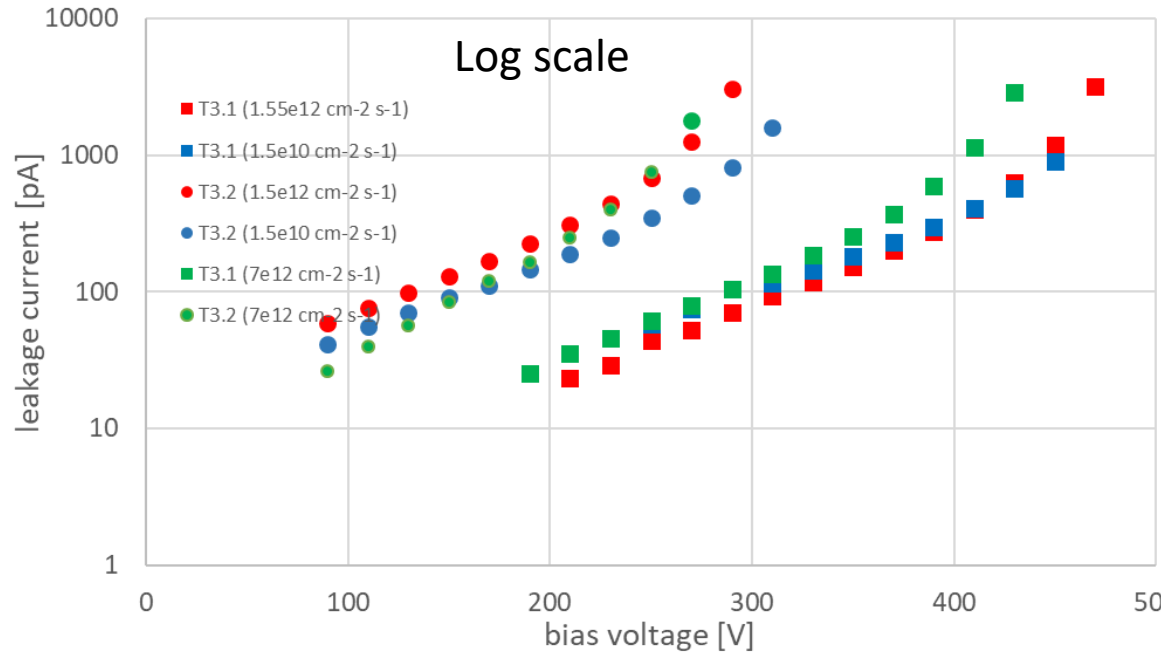


# Charge and Timing measurements

- Timing measurements confirm charge collection measurements – a small difference in voltage is required to achieve the same time resolution.



# Leakage current



Leakage currents at low voltages (generation current) are similar for all three fluxes.

At large bias voltages where  $G(V)$  dominates:

- Same difference in bias voltage for a given current is observed as for the charge:  $V(\phi_1, I) - V(\phi_2, I) = V(\phi_1, Q) - V(\phi_2, Q)$
- Similar relative ratio of current and charge  $I(\phi_1, V) / I(\phi_2, V) = Q(\phi_1, V) / Q(\phi_2, V)$

# Conclusions and future work

- In the investigated flux range of  $10^{10} - 10^{13} \text{ cm}^{-2} \text{ s}^{-1}$  no flux dependence on the damage was found – gain layer and bulk
- The gain and timing performance of all the sensors at high operation voltages was similar – no effects of different flux observed
- This is still 2 orders of magnitude larger than rates at HL-LHC, but it is very probable that the flux effects are not present
- Plans:
  - we can't irradiate for months, so it is not possible to go to much lower fluxes
  - We will go to high fluxes  $10^{15} - 10^{16} \text{ cm}^{-2} \text{ s}^{-1}$  with reactor operating in pulse mode (above critical for very short amount of time) in the following months

# Measurements of gain layer depletion $V_{gl}$

- There is no flux impact on  $V_{gl}$  for both investigated samples with different implant profiles
- We are still two orders of magnitude away from HL-LHC fluxes, but the flux rate seem not to play a role on effective acceptor removal

Estimation of  $V_{gl}$  uncertainty:

$$\sigma_V^2 = \sigma_{c\Phi}^2 + \sigma_{CV}^2 \quad \sigma_{CV} \sim 0.5 \text{ V}$$

$$\sigma_V^2 = c^2 V_{gl}^2 \sigma_\Phi^2 + \sigma_{CV}^2 \quad \sigma_\Phi \sim 0.4 \cdot 10^{14} \text{ cm}^{-2}$$

$$\sigma_V \sim 1.1 \text{ V} \quad c \sim 0.04 \text{ cm}^2$$

The measured values are well within 1 V from the average – so compatible with uncertainty.

